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**July 2013** 

# FGH40T120SMD / FGH40T120SMD\_F155 1200 V, 40 A FS Trench IGBT

### **Features**

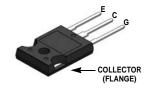
- · FS Trench Technology, Positive Temperature Coefficient
- · High Speed Switching
- Low Saturation Voltage: V<sub>CE(sat)</sub> =1.8 V @ I<sub>C</sub> = 40 A
- 100% of the Parts tested for I<sub>LM</sub>(1)
- · High Input Impedance
- · RoHS Compliant

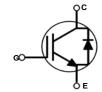
## **Applications**

• Solar Inverter, Welder, UPS & PFC applications.

## **General Description**

Using innovative field stop trench IGBT technology, Fairchild®s new series of field stop trench IGBTs offer the optimum performance for hard switching application such as solar inverter, UPS, welder and PFC applications.





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Description		Ratings	Unit
V <sub>CES</sub>	Collector to Emitter Voltage		1200	V
V <sub>GES</sub>	Gate to Emitter Voltage		±25	V
*GES	Transient Gate to Emitter Voltage		±30	V
l <sub>o</sub>	Collector Current	@ T <sub>C</sub> = 25°C	80	А
I <sub>C</sub>	Collector Current	$@ T_C = 100^{\circ}C$	40	А
I <sub>LM</sub> (1)	Clamped Inductive Load Current	@ T <sub>C</sub> = 25°C	160	A
I <sub>CM</sub> (2)	Pulsed Collector Current		160	A
l <sub>F</sub>	Diode Continuous Forward Current	$@ T_C = 25^{\circ}C$	80	A
•	Diode Continuous Forward Current	@ T <sub>C</sub> = 100°C	40	A
I <sub>FM</sub>	Diode Maximum Forward Current		240	A
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	555	W
• Б	Maximum Power Dissipation	$@ T_C = 100^{\circ}C$	277	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +175	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 second	ds	300	°C

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case		0.27	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case		0.89	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		40	°C/W

Notes: 1. Vcc = 600 V,V\_GE = 15 V, I\_C = 160 A,  $R_G$  = 10  $\Omega_{\odot}$  . Inductive Load 2. Limited by Tjmax

**Package Marking and Ordering Information** 

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
FGH40T120SMD	FGH40T120SMD	TO-247 A03	-	-	30
FGH40T120SMD	FGH40T120SMD_F155	TO-247G03	-	=	30

# Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \text{ uA}$	1200	-	-	V
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}$ , $V_{GE} = 0 V$	-	-	250	uA
I <sub>GES</sub>	G-E Leakage Current	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0 V	-	-	±400	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_C$ = 40 mA, $V_{CE}$ = $V_{GE}$	4.9	6.2	7.5	V
		$I_C = 40 \text{ A}, V_{GE} = 15 \text{ V}$ $T_C = 25^{\circ}\text{C}$	-	1.8	2.4	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 175°C	-	2.0	-	V
Dynamic C	haracteristics					
C <sub>ies</sub>	Input Capacitance		-	4300	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1MHz	-	180	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	1 = 1101112	-	100	-	pF
	Characcteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		-	40	-	ns
t <sub>r</sub>	Rise Time		-	47	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 40 \text{ A},$	-	475	-	ns
t <sub>f</sub>	Fall Time	$R_G = 10 \Omega$ , $V_{GE} = 15 V$ , Inductive Load, $T_C = 25^{\circ}C$	-	10	-	ns
E <sub>on</sub>	Turn-On Switching Loss		-	2.7	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	1.1	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	3.8	-	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	40	-	ns
t <sub>r</sub>	Rise Time		-	55	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 40 \text{ A},$	-	520	-	ns
t <sub>f</sub>	Fall Time	$R_G = 10 \Omega$ , $V_{GE} = 15 V$ ,	-	50	-	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 175°C	-	3.4	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	2.5	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	5.9	-	mJ
Q <sub>g</sub>	Total Gate Charge		-	370	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	$V_{CE} = 600 \text{ V}, I_{C} = 40 \text{ A},$	-	23	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	V <sub>GE</sub> = 15 V	-	210	-	nC

# Electrical Characteristics of the DIODE $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>FM</sub>	Diode Forward Voltage	I <sub>F</sub> = 40 A, T <sub>C</sub> = 25°C	-	3.8	4.8	V
		I <sub>F</sub> = 40 A, T <sub>C</sub> = 175°C	-	2.7	-	V
t <sub>rr</sub>	Diode Reverse Recovery Time	V <sub>R</sub> = 600 V, I <sub>F</sub> = 40 A,	-	65	-	ns
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	$di_F/dt = 200 \text{ A/us}, T_C = 25^{\circ}\text{C}$	-	7.2	-	А
Q <sub>rr</sub>	Diode Reverse Recovery Charge		-	234	-	nC
t <sub>rr</sub>	Diode Reverse Recovery Time	V <sub>R</sub> = 600 V, I <sub>F</sub> = 40 A,	-	200	-	ns
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	$di_F/dt = 200 \text{ A/us}, T_C = 175^{\circ}\text{C}$	-	18.0	-	А
Q <sub>rr</sub>	Diode Reverse Recovery Charge		-	1800	-	nC

Figure 1. Typical Output Characteristics

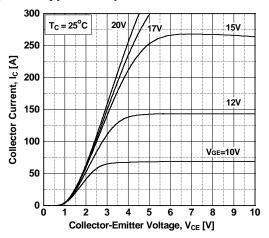


Figure 3. Typical Saturation Voltage Characteristics

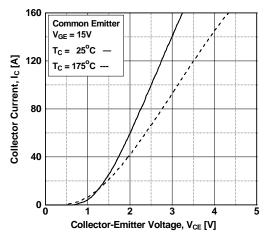
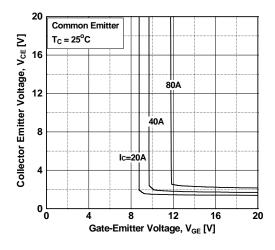


Figure 5. Saturation Voltage vs. V<sub>GE</sub>



**Figure 2. Typical Output Characteristics** 

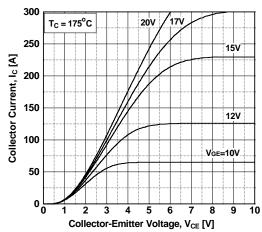


Figure 4. Saturation Voltage vs. Case
Temperature at Variant Current Level

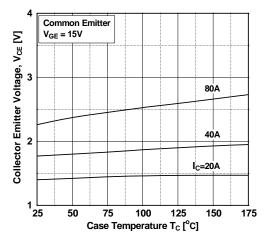


Figure 6. Saturation Voltage vs.  $V_{GE}$ 

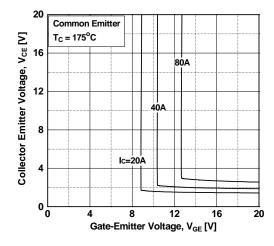


Figure 7. Capacitance Characteristics

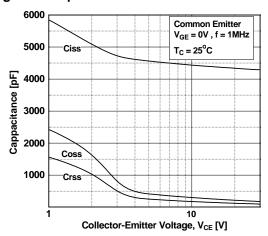


Figure 9. Turn-on Characteristics vs.
Gate Resistance

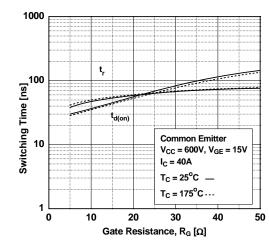


Figure 11. Swithcing Loss vs.

Gate Resistance

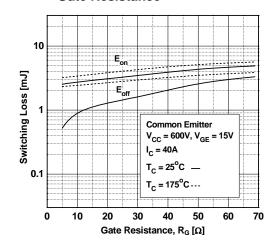


Figure 8. Load Current vs. Frequency

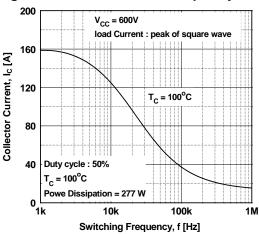


Figure 10. Turn-off Characteristics vs.
Gate Resistance

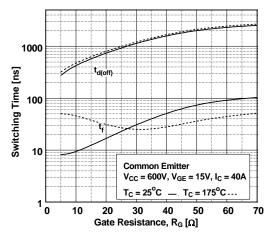


Figure 12. Turn-on Characteristics vs. Collector Current

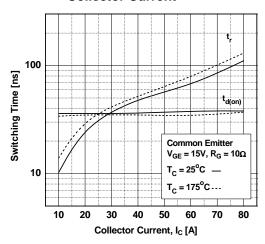


Figure 13. Turn-off Characteristics vs. Collector Current

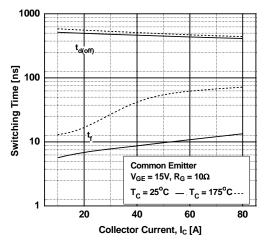


Figure 15. Gate Charge Characteristics

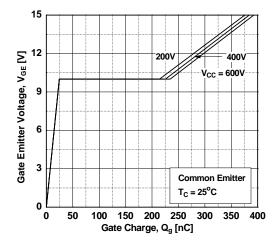


Figure 17. Forward Characteristics

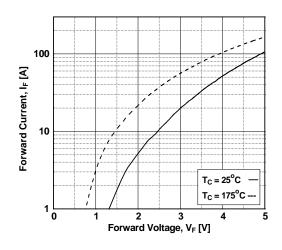


Figure 14. Swithcing Loss vs. Collector Current

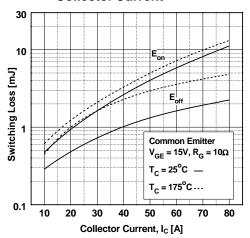


Figure 16. SOA Characteristics

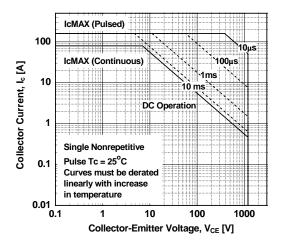


Figure 18. Reverse Recovery Current

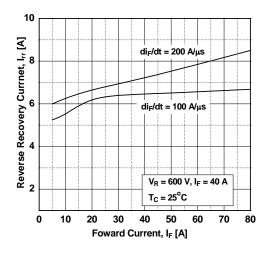


Figure 19. Reverse Recovery Time

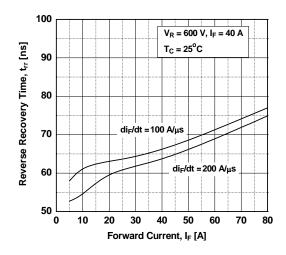


Figure 20. Stored Charge

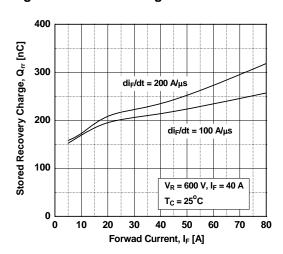
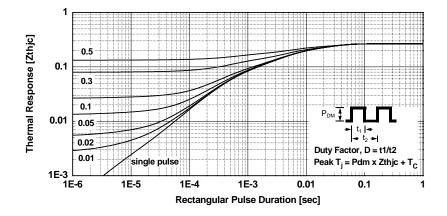
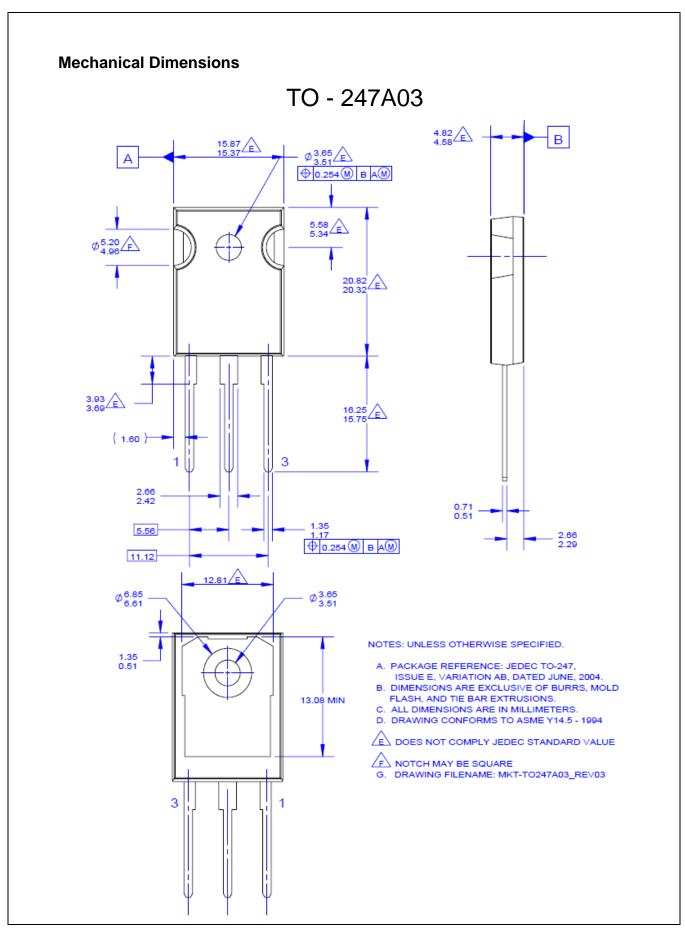


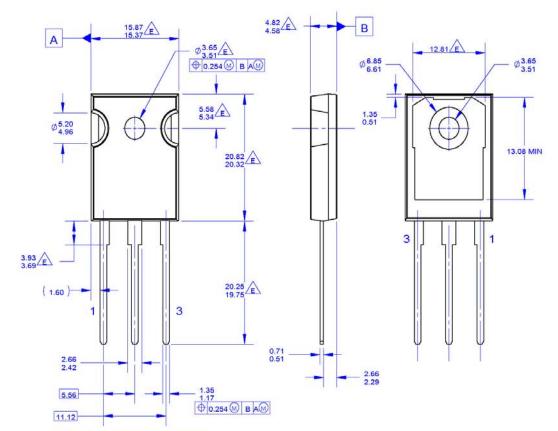
Figure 21. Transient Thermal Impedance of IGBT





## **Mechanical Dimensions**

# TO-247G03



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